

**SOT-23 BIPOLAR TRANSISTORS
TRANSISTOR(PNP)**

FEATURES

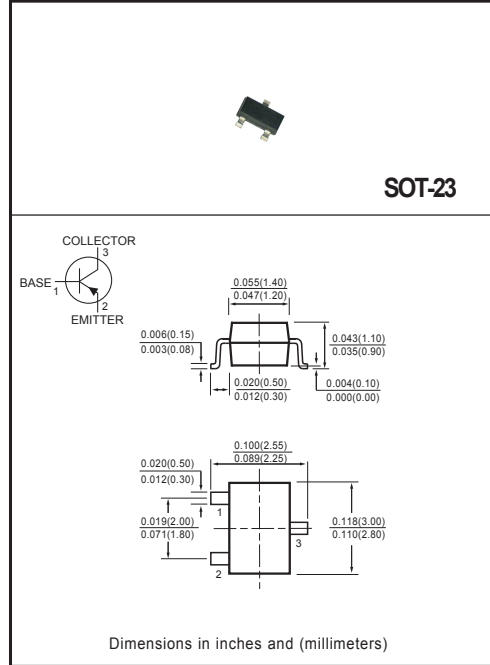
- * Power dissipation
P_{CM} : 0.33 W (T_{amb}=25°C)
- * Collector current
I_{CM} : -0.8 A
- * Collector-base voltage
V_{(BR)CBO} : -60 V
- * Operating and storage junction temperature range
T_J,T_{stg}: -55°C to +150°C

MECHANICAL DATA

- * Case: Molded plastic
- * Epoxy: UL 94V-O rate flame retardant
- * Lead: MIL-STD-202E method 208C guaranteed
- * Mounting position: Any
- * Weight: 0.008 gram

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.
Single phase , half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.



ELECTRICAL CHARACTERISTICS (@ TA = 25°C unless otherwise noted)

CHARACTERISTICS	SYMBOL	MIN	TYP	MAX	UNITS
Collector-base breakdown voltage (I _C = -10μA, I _E =0)	V _{(BR)CBO}	-60	-	-	V
Collector-emitter breakdown voltage (I _C = -10mA, I _B =0)	V _{(BR)CEO}	-45	-	-	V
Emitter-base breakdown voltage (I _E = -10μA, I _C =0)	V _{(BR)EBO}	-5	-	-	V
Collector cut-off current (V _{CB} = -45V, I _E =0)	I _{CBO}	-	-	-0.02	μA
Collector cut-off current (V _{EB} = -4V, I _C =0)	I _{EBO}	-	-	-0.02	μA
DC current gain (V _{CE} = -10V, I _C = -0.1mA)	h _{FE}	50	-	-	-
DC current gain (V _{CE} = -1V, I _C = -10mA)		120	-	-	-
DC current gain (V _{CE} = -1V, I _C = -100mA)		160	-	400	-
DC current gain (V _{CE} = -2V, I _C = -500mA)		60	-	-	-
Collector-emitter saturation voltage (I _C = -100mA, I _B = -10mA)	V _{CE(sat)}	-	-	-0.3	V
Collector-emitter saturation voltage (I _C = -500mA, I _B = -50mA)	V _{CE(sat)}	-	-	-0.7	V
Base-emitter saturation voltage (I _C = -100mA, I _B = -10mA)	V _{BE(sat)}	-	-	-1.25	V
Base-emitter saturation voltage (I _C = -500mA, I _B = -50mA)		-	-	-2	V
Transition frequency (V _{CE} = -10V, I _C = -20mA, f=100MHz)	f _r	100	-	-	MHz
Output capacitance (V _{CB} = -10V, I _E = 0, f=1MHz)	C _{ob}	-	-	18	pF
Input capacitance (V _{EB} = -0.5V, I _E = 0, f=1MHz)	C _{ib}	-	-	80	pF
Noise figure (V _{CE} = -5V, I _E = -0.2mA, f=1kHz, Δf=200Hz, R _G =1KΩ)	NF	-	-	10	dB

Marking	DG
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Note 1: "Fully ROHS compliant", "100% Sn plating (Pb-free)".

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